



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ying Zhou, et al. § Group Art Unit: 2812  
Serial No.: 10/696,204 §  
Filed: October 29, 2003 § Examiner:  
For: Depositing an Oxide § Atty. Dkt. No.: ITL.1024US (P16711)  
§

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant submits the references listed on the attached form PTO 1449 together with any required copies of such references.

This statement is being filed before the receipt of a first Office action on the merits.

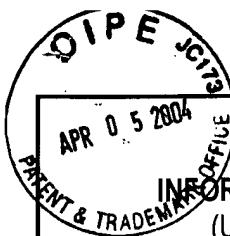
Please apply any charges or credits to Deposit Account 20-1504 (ITL.1024US).

Respectfully submitted,

Date: April 2, 2004

Rhonda L. Sheldon  
Registration No. 50,457  
TROP, PRUNER & HU, P.C.  
8554 Katy Freeway, Suite 100  
Houston, Texas 77024  
(713) 468-8880 [Phone]  
(713) 468-8883 [Fax]

|   |
|---|
| Date of Deposit: <u>April 2, 2004</u>   |
| I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as <b>first class mail</b> with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. |
| Rebecca R. Ginn   |



|   |                                |  |   |            |
|---|--------------------------------|--|---|------------|
| <b>INFORMATION DISCLOSURE CITATION</b><br>(Use several sheets if necessary) |                                |  | ATTY DOCKET NO.                           | SERIAL NO. |
|   |                                |  | ITL.1027US (P16711)                       | 10/696,204 |
|   |                                |  | APPLICANT(S):<br><b>YING ZHOU, ET AL.</b> |            |
| FILING DATE:<br><b>October 29, 2003</b>                                     | GROUP ART UNIT:<br><b>2812</b> |  |   |            |

### U.S. PATENT DOCUMENTS

| *EXAMINE R INITIAL |    | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|--------------------|----|-----------------|------|------|-------|----------|----------------------------|
|                    | A. |                 |      |      |       |          |                            |
|                    | B. |                 |      |      |       |          |                            |
|                    | C. |                 |      |      |       |          |                            |
|                    | D. |                 |      |      |       |          |                            |
|                    | E. |                 |      |      |       |          |                            |
|                    | F. |                 |      |      |       |          |                            |
|                    | G. |                 |      |      |       |          |                            |
|                    | H. |                 |      |      |       |          |                            |
|                    | I. |                 |      |      |       |          |                            |

### FOREIGN PATENT DOCUMENTS

|  |    | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION |    |
|--|----|-----------------|------|---------|-------|----------|-------------|----|
|  |    |                 |      |         |       |          | YES         | NO |
|  | J. |                 |      |         |       |          |             |    |
|  | K. |                 |      |         |       |          |             |    |
|  | L. |                 |      |         |       |          |             |    |
|  | M. |                 |      |         |       |          |             |    |
|  | N. |                 |      |         |       |          |             |    |
|  | O. |                 |      |         |       |          |             |    |

### OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

|    |  |
|----|--|
| P. | Robert M. Wallace, "Challenges for the Characterization and Integration of High-k Gate Dielectrics," pp. 1-50, Nov. 2002, <a href="http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf">http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf</a>  |
| Q. | Gerry Lucovsky, "The Physics and Chemistry of High-k Dielectrics and their Interfaces," pp. 1-49, available on June 2003, at <a href="http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf">http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf</a> |
| R. |  |
| S. |  |
| T. |  |

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.